

## ABSTRACT OF THE DISCLOSURE

### COMPOSITIONS AND METHODS USING SAME FOR CARBON DOPED SILICON CONTAINING FILMS

Described herein are compositions and methods using same for forming a  
5 silicon-containing film such as, without limitation, a carbon doped silicon oxide film, a  
carbon doped silicon nitride, a carbon doped silicon oxynitride film in a deposition  
process. In one aspect, the composition comprises at least cyclic carbosilane having at  
least one Si-C-Si linkage and at least one anchoring group selected from a halide atom,  
an amino group, and combinations thereof.

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FIG. 1